

Test Data Sheet

PM7 - MWIR

(EO-12.5T3-MIR)

S/N: J6716

Resonant electro-optic phase modulator

with

- temperature sensor (NTC)

- thermal crystal mount

- DC port (SMA)

| RF properties | Value | Unit |
|--|-------------|------|
| Preset resonance frequency: f_0 ¹⁾ | 12.5 | MHz |
| Resonance frequency tuning range: Δf_0 ¹⁾ | 11.0 - 13.8 | MHz |
| RF Bandwidth: Δv_{RF} | 140 | kHz |
| Quality factor: Q | 89 | |
| Required RF power for 1rad @ 4500nm ²⁾ | 33.7 | dBm |
| max. RF power: RF_{max} ³⁾ | 1 | W |

| DC properties | Value | Unit |
|---|---------|------|
| DC Bandwidth: Δv_{DC} (-3dB) | ~ 9 | kHz |
| Required DC voltage for π rad (PM) @ 4500nm | 1.7 | kVdc |
| max. DC voltage: V_{max} | +/- 500 | Vdc |
| Input capacitance (DC) | 1.0 | nF |

| Optical properties | | |
|---|---------------|-------------------|
| EO crystal | LT | |
| Aperture | 3x3 | mm ² |
| Wavefront distortion (633nm) | $< \lambda/6$ | nm |
| recommended max. optical intensity (4500nm) | < 1 | W/mm ² |
| AR coating ($R_{avg} < 1\%$) | 3.0 - 4.5 | um |

¹⁾ at 24.3°C ²⁾ with 50Ω termination ³⁾ no damage with $RF_{in} < 2W$

Measured modulation

Fig. 1: Oscilloscope trace

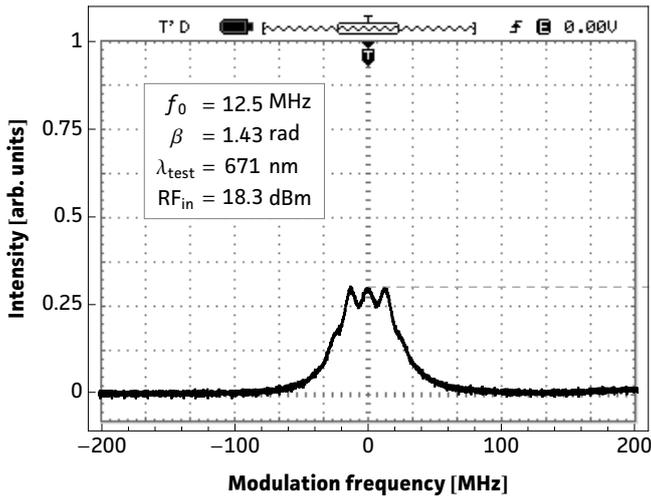


Fig. 2: Carrier/sideband ratio

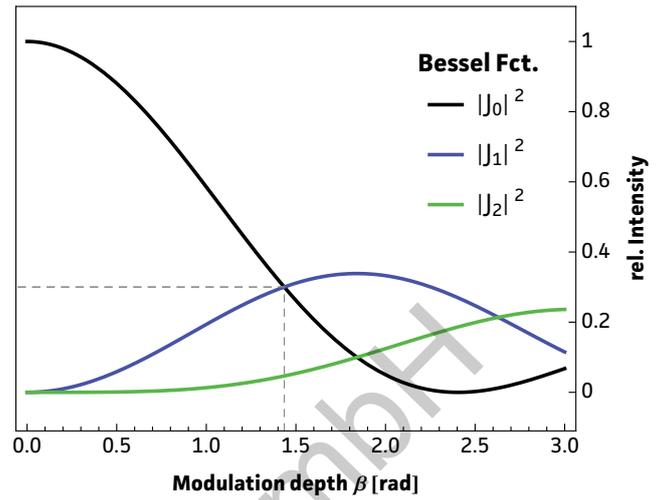


Table 1: Expected modulation

| $\beta = 1 \text{ rad}$ | unit | λ_1 | λ_2 | λ_3 |
|-------------------------|-------|-------------|-------------|-------------|
| λ | nm | 671 | 3000 | 4500 |
| P | dBm | 15.2 | 29.3 | 33.7 |
| P | W | 0.03 | 0.85 | 2.34 |
| U | V_p | 1.8 | 9.2 | 15.3 |
| U_π | V_p | 5.7 | 29. | 48. |
| β/U | rad/V | 0.55 | 0.11 | 0.07 |

Fig.1: Recorded oscilloscope trace retrieved from a test setup as illustrated below.

Fig.2: Squared absolute values of first-kind Bessel functions vs. modulation depth. Vertical lines reveal the ratio between the carrier $|J_0|^2$ and the i^{th} sideband $|J_i|^2$ at a specific β .

Fig.3: Dependency between RF amplitude and modulation depth for different wavelengths. Points on the curve allow to retrieve either the required RF amplitude for a specific/desired β or the max. achievable modulation depth for a given/available RF power.

Table 1: Expected RF-amplitude/-power values and conversion factors for the required wavelength at the reference modulation depth of 1 rad. **Note:** Experimentally recorded modulation depth displayed in Fig.1 might vary from the respective values ($\beta=1\text{rad}$) provided in the table.

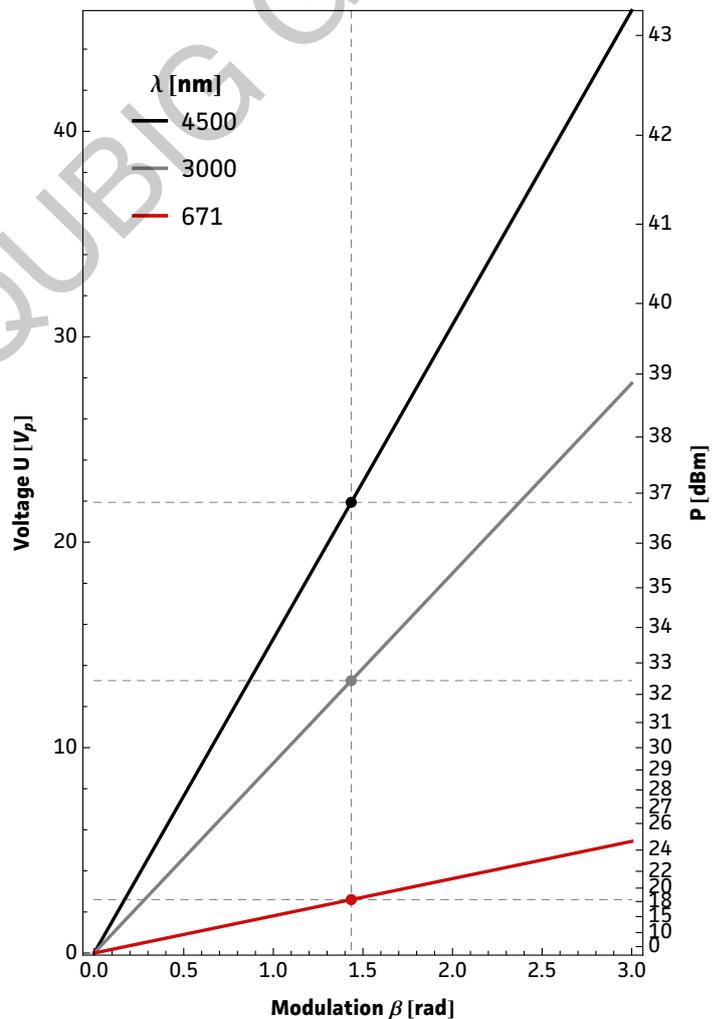
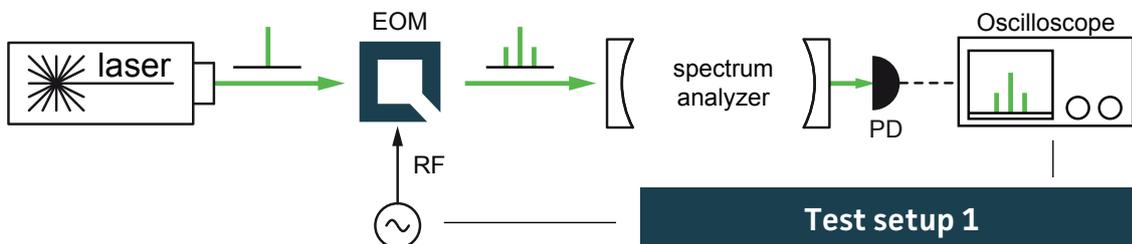
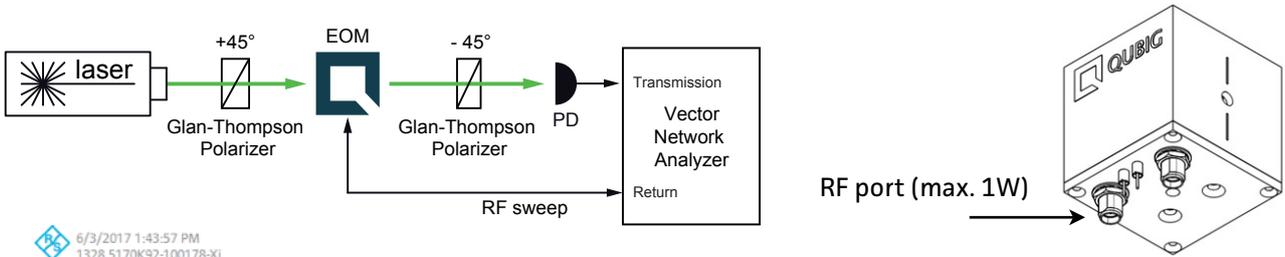


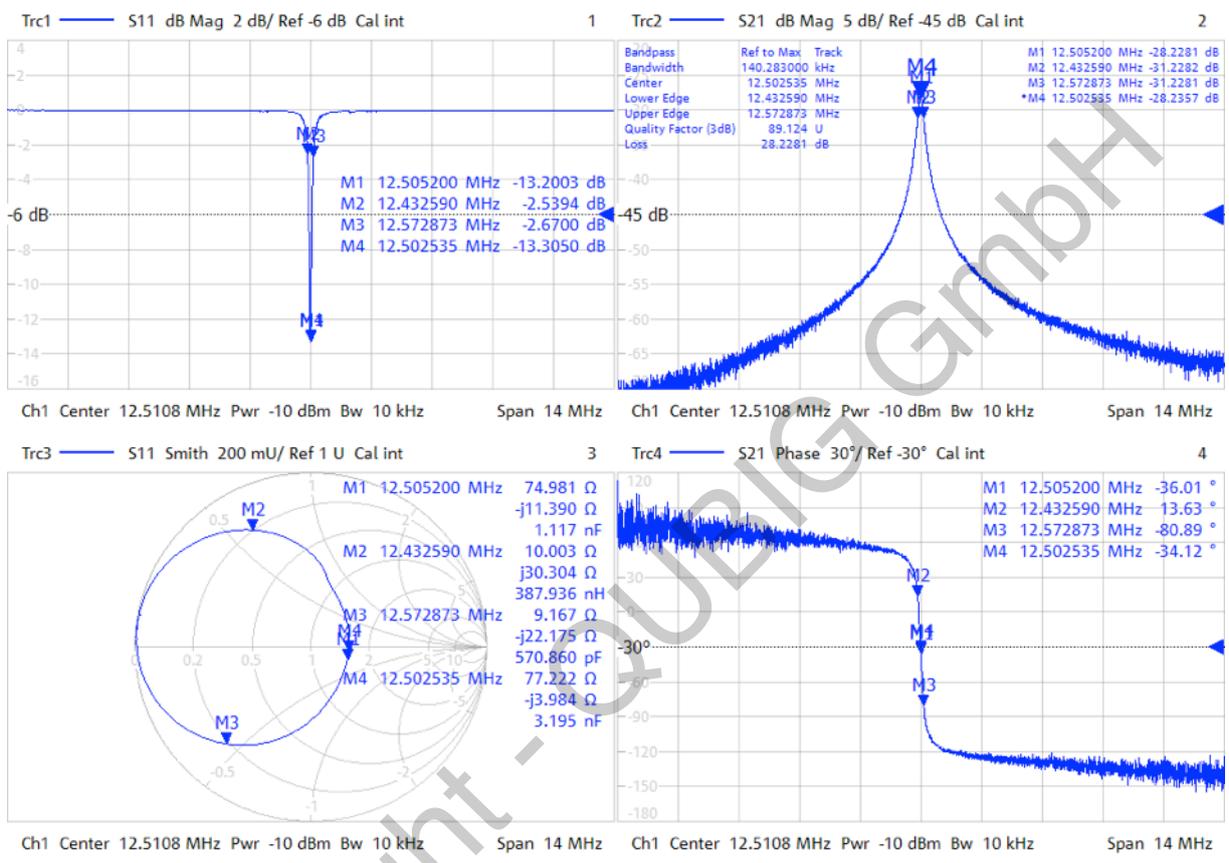
Fig. 3: RF-signal amplitude vs. modulation depth



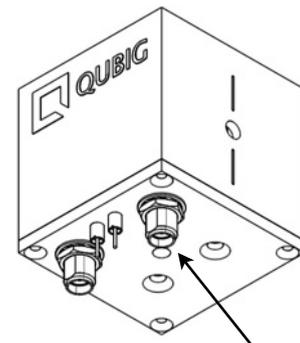
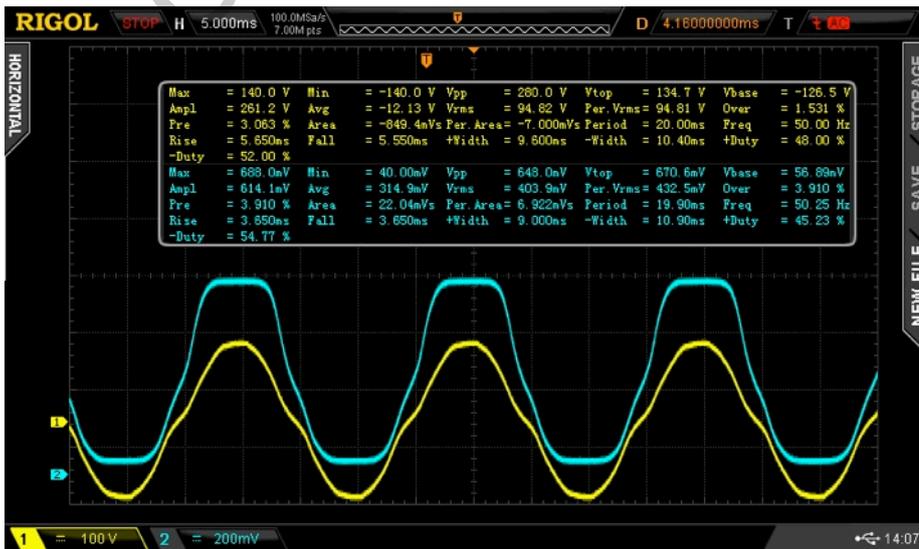
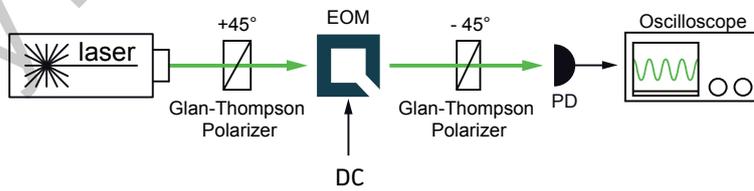
Resonance characteristics



6/3/2017 1:43:57 PM
1328.5170K92-100178-XI



DC characteristics



DC port (max. +/-500V)

yellow:
DC Voltage input signal

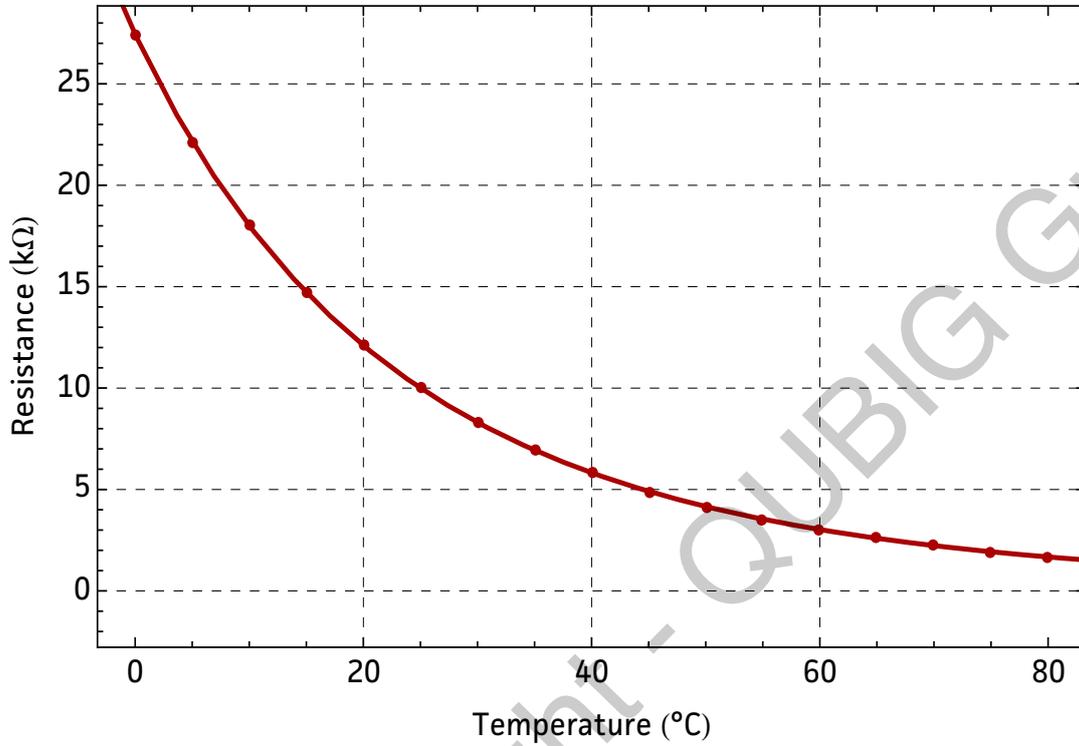
blue:
optical modulation
(achieved modulation depth: π)

TXC-option information

NTC characteristics:

| NTC part number | Resistance (25°C) (ohm) | B-Constant (25-50°C) (K) | Operating Current for Sensor (25°C) (mA) | Rated Electric Power (25°C) (mW) | Typical Dissipation Constant (25°C) (mW/°C) | Thermal Time Constant (25°C) (s) |
|--------------------|-------------------------|--------------------------|--|----------------------------------|---|----------------------------------|
| NXFT15XH103FA2B050 | 10k +/- 1% | 3380 +/- 1% | 0.12 | 7.5 | 1.5 | 4 |

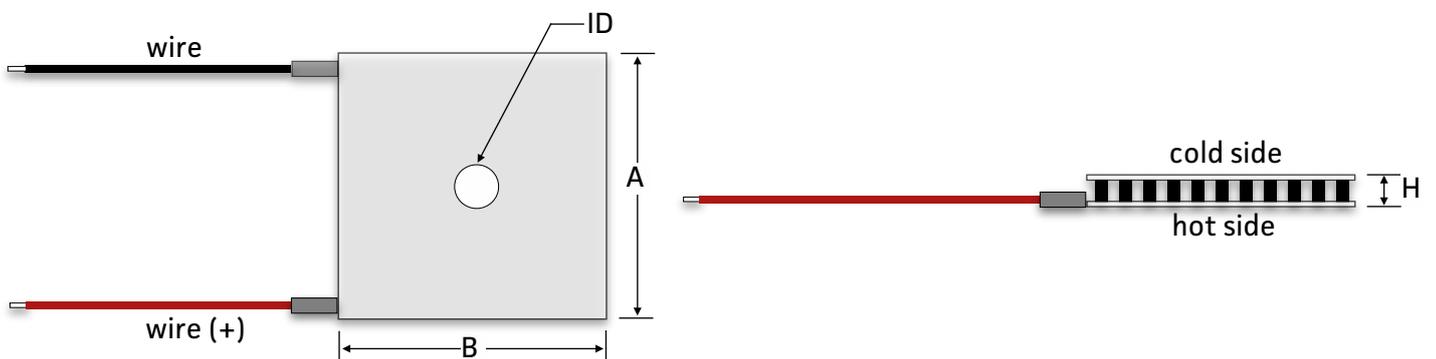
- Operating Current for Sensor rises Thermistor's temperature by 0.1°C
- Rated Electric Power shows the required electric power that causes Thermistors's temperature to rise to 30°C by self heating, at ambient temperature of 25°C.



| Part Number | NXFT15XH103 |
|-------------|-----------------|
| Resistance | 10kΩ |
| B-Constant | 3380K |
| Temp. (°C) | Resistance (kΩ) |
| -40 | 197.388 |
| -35 | 149.395 |
| -30 | 114.345 |
| -25 | 88.381 |
| -20 | 68.915 |
| -15 | 54.166 |
| -10 | 42.889 |
| -5 | 34.196 |
| 0 | 27.445 |
| 5 | 22.165 |
| 10 | 18.010 |
| 15 | 14.720 |
| 20 | 12.099 |
| 25 | 10.000 |
| 30 | 8.309 |
| 35 | 6.939 |
| 40 | 5.824 |
| 45 | 4.911 |
| 50 | 4.160 |
| 55 | 3.539 |
| 60 | 3.024 |
| 65 | 2.593 |
| 70 | 2.233 |
| 75 | 1.929 |
| 80 | 1.673 |
| 85 | 1.455 |
| 90 | 1.270 |
| 95 | 1.112 |
| 100 | 0.976 |
| 105 | 0.860 |
| 110 | 0.759 |
| 115 | 0.673 |
| 120 | 0.598 |
| 125 | 0.532 |

TEC characteristics:

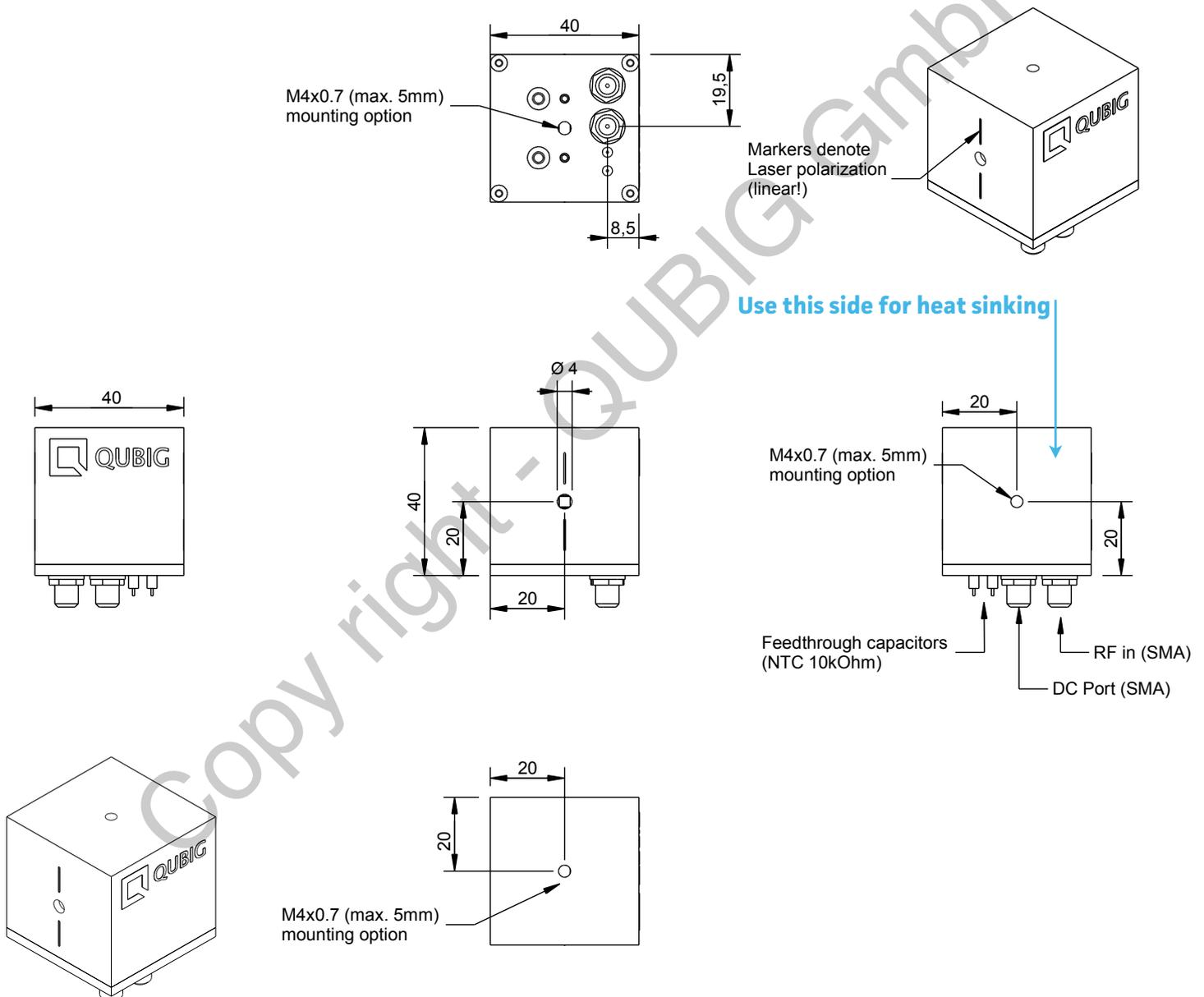
| TEC part number | I _{max} (A) | U _{max} (V) | Q _{cmax} (W) | ΔT _{max} (K) | T _{max} (°C) | A (mm) | B (mm) | H (mm) | ID (mm) | Sealing |
|-----------------------|----------------------|----------------------|-----------------------|-----------------------|-----------------------|--------|--------|--------|---------|---------|
| UEPT-440-127-040M125S | 4.0 | 15.2 | 40 | 67.0 | 125.0 | 40.0 | 40.0 | 4.6 | 4.5 | Silicon |



Handling instructions

- Input laser polarization must be aligned with respect to the white markers on the housing
- Please handle device carefully. Avoid shock. Don't drop.
- After turn on the resonance frequency might drift slightly with applied RF power. Please compensate by tuning the RF drive frequency until steady-state (~min).
- Slight angle adjustment can reduce unwanted residual amplitude modulation (RAM)

Package drawing



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